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(54) **THERMALLY IMPROVED PCB FOR  
SEMICONDUCTOR POWER DIE  
CONNECTED BY VIA TECHNIQUE AND  
ASSEMBLY USING SUCH PCB**

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**ABSTRACT**

Power module comprising a power semiconductor die and at least one substrate comprising an insulating layer in contact with a metallized connection surface of said die and at least one conductive path on a conductive layer on a face of the insulating layer opposite to the metallized connection surface of the die and wherein said insulating layer comprises vias filled with conductive material to provide connecting pads between said metallized connection surface of said die and said conductive path, and wherein said vias are arranged with a decreasing density from at least one hot spot position of said metallized connection surface when the die is in operation to a peripheral area of said metallized connection surface.

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